

APR. 12. 2004 1:54PM

BSKB

NO. 643 P. 1

P.O. Box 747
Falls Church, Virginia 22040-0747
Phone: (703) 205-8000
Fax: (703) 205-8050
(703) 698-8590 (GIV)

Birch, Stewart, Kolasch & Birch, LLP

Fax

RECEIVED
CENTRAL FAX CENTER

APR 12 2004

OFFICIAL

To:	USPTO	From:	Hyung N. Sohn, P.
Fax:	703-872-9306	Date:	4 /12/04
Phone:		Pages:	4 (including cover sheet)
Your Ref.:	U.S. Appln. 09/720,084	Our Ref.:	3672-0109P
Re:	Applicant Initiated Interview Request Form.	CC:	
<input type="checkbox"/> Urgent <input checked="" type="checkbox"/> For Review <input type="checkbox"/> Please Comment <input type="checkbox"/> Please Reply <input type="checkbox"/> Please Recycle			

This transmission is intended for the sole use of the individual and entity to whom it is addressed, and may contain information that is privileged, confidential, and exempt from disclosure under applicable law. You are hereby notified that any dissemination, distribution, or duplication of this transmission by someone other than the intended addressee or its designated agent is strictly prohibited. If your receipt of this transmission is in error, please notify this firm immediately by collect call to (703) 205-8000, and send the original transmission to us by return mail at the address above.

Comments:

ATTN: Examiner K. Kianni, Art Unit 2877

Applicant Initiated Interview Request Form

Application No. 09/120084 First Named Applicant: Thomas EBBESAN
 Examiner: K. Kianni Art Unit: 2877 Status of Application: After-Final
Notice of Appeal
filed
 Tentative Participants:
 (1) Hyung Sohn (2) Geirr Leisstad
 (3) K. Kianni (4) Supervisor
 Proposed Date of Interview: 4/19 Proposed Time: 11:00 (AM/PM)
 Type of Interview Requested:
 (1) ☐ Telephonic (2) ☒ Personal (3) ☐ Video Conference
 Exhibit To Be Shown or Demonstrated: ☐ YES ☐ NO
 If yes, provide brief description: _____

Issues To Be Discussed

Issues (Rej., Obj., etc)	Claims/ Fig. #s	Prior Art	Discussed	Agreed	Not Agreed
(1) <u>Rejection</u>	<u>2-32, 35-52</u>	<u>Gudesen et al.</u>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
(2) <u>Rejection</u>	<u>55-56</u>	_____	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
(3) _____	_____	_____	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
(4) _____	_____	_____	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

☒ Continuation Sheet Attached

Brief Description of Arguments to be Presented:

see Attached

An interview was conducted on the above-identified application on _____.

NOTE:

This form should be completed by applicant and submitted to the examiner in advance of the interview (see MPEP § 713.01).

This application will not be delayed from issue because of applicant's failure to submit a written record of this interview. Therefore, applicant is advised to file a statement of the substance of this interview (37 CFR 1.133(b)) as soon as possible.

Hyung Sohn
 (Applicant's Representative Signature)

 (Examiner/SPE Signature)

This collection of information is required by 37 CFR 1.133. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 21 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.

Attachment to Interview Request form 413-A for Application 09/720,084

Examiner Kianni:

We hope the following will comply with your request for more details regarding the discussion items for the above-identified application:

There are many issues. However, we will mainly discuss claim 35 since it is the only independent claim (among the currently pending claims).

- Gudesen et al cannot be relied upon to render claim 35 obvious:
 - Claim 35 recites, in part, "wherein said elements are arranged in said predetermined circuit pattern by integrating said elements using weaving, knitting, crocheting, knotting, or stitching."
 - Figures 1a - 3b show some examples of this "weaving, knitting, crocheting, knotting, or stitching" results.
 - One of the distinguishing feature is that a strand (or element) in a first layer crosses a strand in a second layer above the second layer at one cross-point and below the second layer at another cross-point.
 - For example, see figures 2a - 2e.
 - Gudesen does NOT teach "weaving, knitting, ..."
 - Gudesen is a Read Only Memory (ROM) manufactured in conventional method - on a layer by layer basis.
 - Figures 3a and 3b of Gudesen (cited by you) clearly shows horizontally laid group of electrodes 4 are ENTIRELY formed above the vertically laid group of electrodes 2.
 - The memory cells 5 are formed and data is written to the ROM by either leaving the memory material 9 to contact both

electrodes 2 and 4 at the crossing or by isolating the contact (through using isolator patch 7) at the crossing.

- The layer-by-layer conventional process CANNOT produce the weaving, knitting, ... pattern as shown in figures 1a - 3b.
- o Gudesen does NOT suggest "weaving, knitting, ..."
 - The layer-by-layer conventional process TEACHES AWAY.
 - Gudesen's page 4, lines 3-8 CANNOT be relied upon to suggest the feature as asserted
 - The relied upon portion states:

The use of organic materials, for instance polymer materials, which realized in thin film technology may be used both in conductors, isolators, and semiconductors materials, something which supposedly shall provide more **flexible technical solutions** and especially a much reduced cost than would be the case when using crystalline inorganic semiconductors.
Emphasis added.

- At best, the term "flexible technical solution" can be interpreted as providing a "choice" of solutions.
- This CANNOT be interpreted to mean flexible in a physical sense.
- Indeed, the layer-by-layer approach described in Gudesen would suggest that the ROM device is rigid.

Other items:

- Gudesen does NOT teach a "fabric-like" structure - Figure 3a of Gudesen shows a layer-by-layer manufacturing result - i.e. electrodes of one layer is ENTIRELY above the electrodes of another layer - this is NOT fabric-like
- Isolator 6 is LOCALIZED - cannot qualify as an element as claimed as asserted in the Office Action (see page 3 of Final Office Action).
- Gudesen does not teach or suggest exposing active regions by removing shielding 3 as asserted (see page 4 of Final Office Action) - 3 is a substrate.
- Many others.